

N-Channel Enhancement Mode Power MOSFET

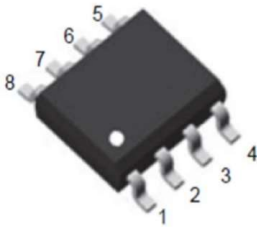
Features

- $V_{DS} = 200V$, $I_D = 3A$
- $R_{DS(ON)} < 260\text{ m}\Omega$ @ $V_{GS} = 10V$
- $R_{DS(ON)} < 310\text{ m}\Omega$ @ $V_{GS} = 4.5V$

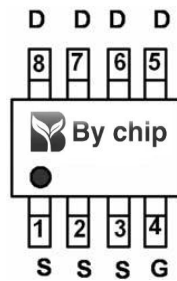
General Features

- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free and Green Available

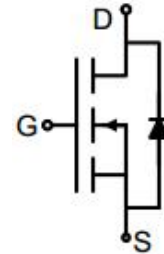
100% UIS TESTED!
100% ΔV_{ds} TESTED!



SOP-8



pin assignment



Schematic diagram

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175\text{ }^\circ\text{C}$) ^b	I_D	$T_C = 25\text{ }^\circ\text{C}$	A
		$T_C = 125\text{ }^\circ\text{C}$	
Pulsed Drain Current	I_{DM}	10	A
Continuous Source Current (Diode Conduction)	I_S	6	
Avalanche Current	I_{AS}	6	mJ
Single Pulse Avalanche Energy	E_{AS}	18	
Maximum Power Dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}$	W
		$T_A = 25\text{ }^\circ\text{C}$	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^a	R_{thJA}	$t \leq 10\text{ s}$	15	18	$^\circ\text{C/W}$
		Steady State	40	50	
Junction-to-Case (Drain)	R_{thJC}	0.85	1.1		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

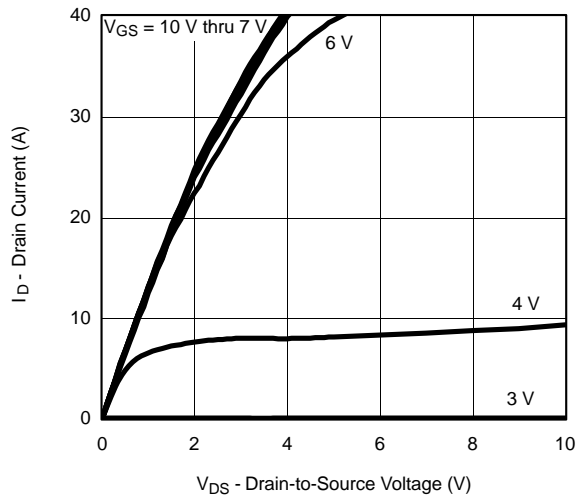
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	200			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3\text{ A}$		0.260		Ω
		$V_{GS} = 10\text{ V}, I_D = 3\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.310		
		$V_{GS} = 10\text{ V}, I_D = 3\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.330		
		$V_{GS} = 6\text{ V}, I_D = 3\text{ A}$		0.292		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 3\text{ A}$		35		S
Dynamic^a						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, F = 1\text{ MHz}$		1800		pF
Output Capacitance	C_{oss}			180		
Reverse Transfer Capacitance	C_{rss}			80		
Total Gate Charge ^c	Q_g	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 3\text{ A}$		34	51	nC
Gate-Source Charge ^c	Q_{gs}			8		
Gate-Drain Charge ^c	Q_{gd}			12		
Gate Resistance	R_g		0.5		2.9	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 5.2\text{ }\Omega$ $I_D \cong 3\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		15	25	ns
Rise Time ^c	t_r			50	75	
Turn-Off Delay Time ^c	$t_{d(off)}$			30	45	
Fall Time ^c	t_f			60	90	
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$)						
Pulsed Current	I_{SM}				5	A
Diode Forward Voltage ^b	V_{SD}	$I_F = 3\text{ A}, V_{GS} = 0\text{ V}$		0.9	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		180	250	ns

Notes:

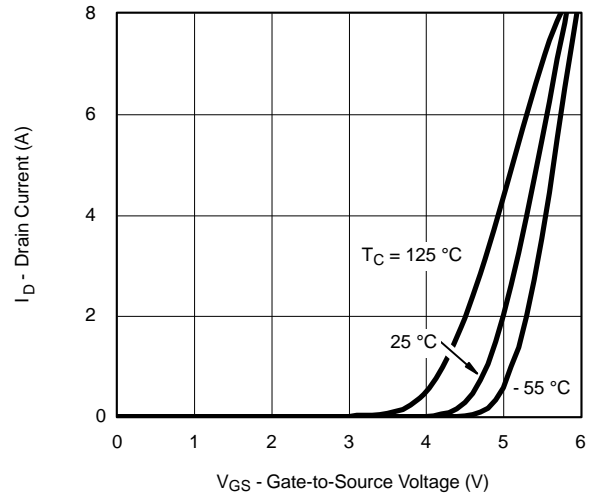
- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

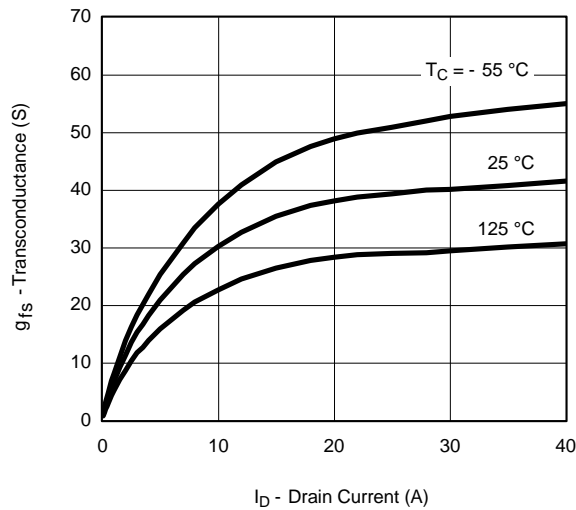
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



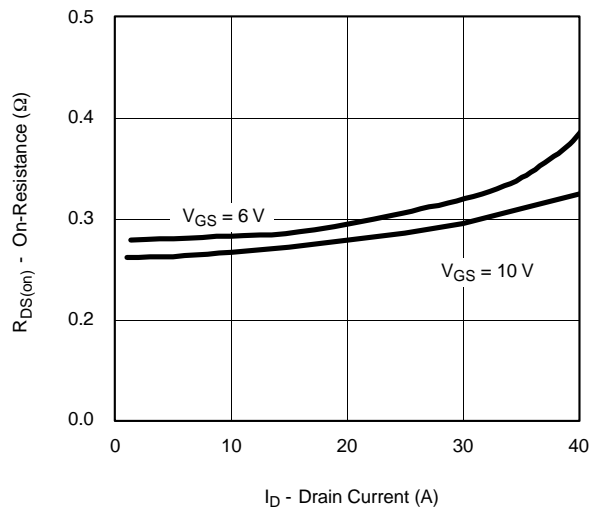
Output Characteristics



Transfer Characteristics



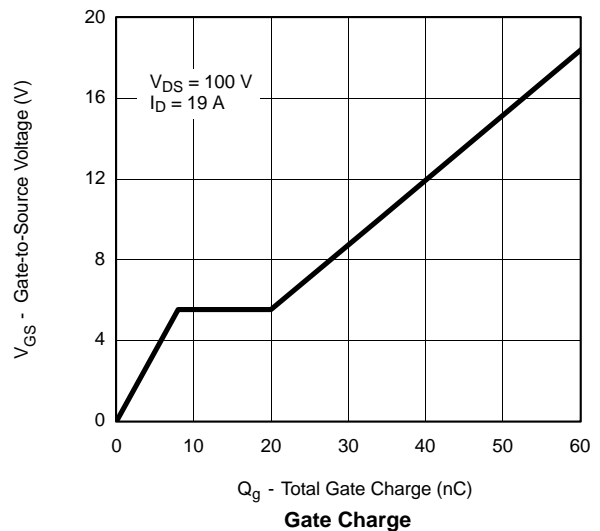
Transconductance



On-Resistance vs. Drain Current



Capacitance



Gate Charge

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

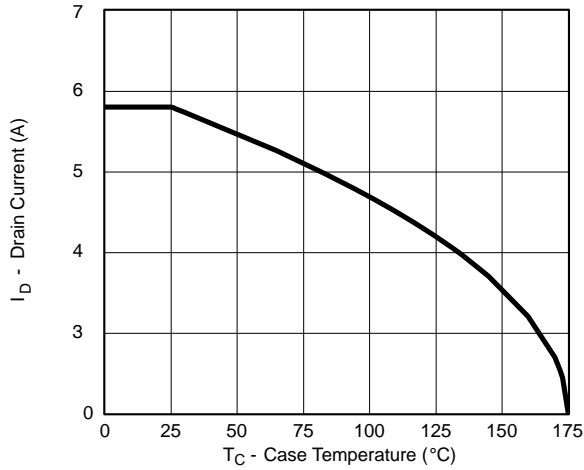


On-Resistance vs. Junction Temperature

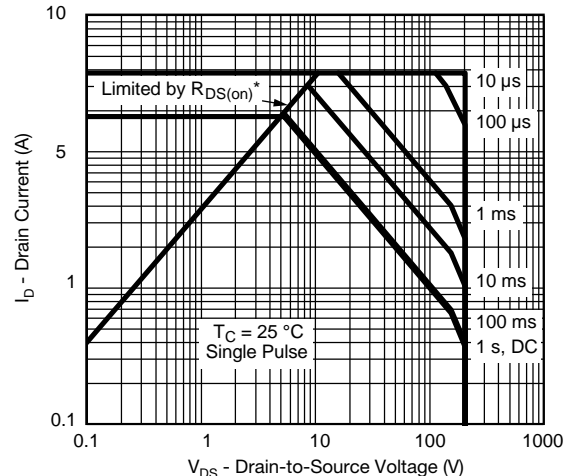


Source-Drain Diode Forward Voltage

THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case